



PATENT ABSTRACTS OF JAPAN

(11) Publication number: **2002111054 A**

(43) Date of publication of application: **12.04.02**

(51) Int. Cl. **H01L 33/00**
H01S 5/183

(21) Application number: 2000299425

(22) Date of filing: 29.09.00

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(54) VERTICAL RESONATOR TYPE
SEMICONDUCTOR LIGHT EMITTING ELEMENT
AND VERTICAL RESONATOR TYPE
SEMICONDUCTOR LIGHT EMITTING DEVICE

(57) **Abstract:**

PROBLEM TO BE SOLVED: To obtain an element which has no characteristic deterioration due to moisture absorption and high reliability as a vertical resonator type semiconductor element which uses AlGaAs of high Al composition for a substrate- surface side DBR mirror.

SOLUTION: On the substrate-surface side DBR mirror, a semiconductor layer including an InGaP layer functioning as a dampproof layer is provided to stop the AlGaAs-based DBR mirror of high Al composition from deteriorating in characteristics owing to moisture absorption.

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